

# Thyristor Module

$V_{RRM}$  = 1400 V  
 $I_{TAV}$  = 300 A  
 $V_T$  = 1,02 V

1~ Triac

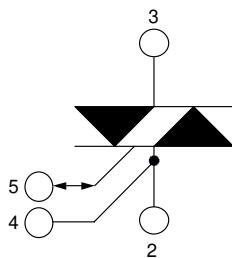
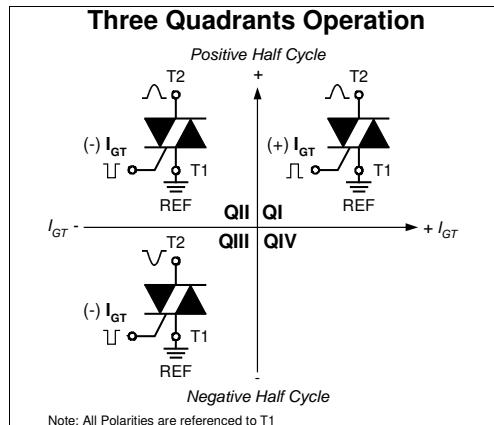
Part number

**MCMA650MT1400NKD**



Backside: isolated

 E72873



## Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation - QI - QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

## Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

## Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

## Disclaimer Notice

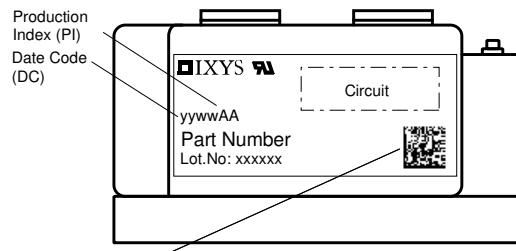
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**Rectifier**

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1500	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1400	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1400 V$ $V_{R/D} = 1400 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1 40	mA
$V_T$	forward voltage drop	$I_T = 300 A$ $I_T = 600 A$ $I_T = 300 A$ $I_T = 600 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1,09 1,26 1,02 1,23	V
$I_{TAV}$	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 140^\circ C$		300	A
$I_{RMS}$	RMS forward current per phase	180° sine			650	A
$V_{TO}$	threshold voltage	$r_T$ slope resistance } for power loss calculation only	$T_{VJ} = 140^\circ C$		0,81	V
	slope resistance				0,68	mΩ
$R_{thJC}$	thermal resistance junction to case				0,12	K/W
$R_{thCH}$	thermal resistance case to heatsink			0,04		K/W
$P_{tot}$	total power dissipation		$T_C = 25^\circ C$		960	W
$I_{TSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 140^\circ C$ $V_R = 0 V$		9,60 10,4 8,16 8,82	kA
$I^2t$	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 140^\circ C$ $V_R = 0 V$		460,8 447,4 332,9 323,3	kA²s
$C_J$	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	438		pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$ $t_p = 300 \mu s$	$T_C = 140^\circ C$		120 60 20	W
$P_{GAV}$	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^\circ C; f = 50 \text{ Hz}$ repetitive, $I_T = 900 A$ $t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ $I_G = 1 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 300 A$			100	A/μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$T_{VJ} = 140^\circ C$		1000	V/μs
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		2 3	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		220 400	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ C$		0,25	V
$I_{GD}$	gate non-trigger current				10	mA
$I_L$	latching current	$t_p = 30 \mu s$ $I_G = 1 A; di_G/dt = 1 A/\mu s$	$T_{VJ} = 25^\circ C$		200	mA
$I_H$	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		150	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 1 A; di_G/dt = 1 A/\mu s$	$T_{VJ} = 25^\circ C$		2	μs
$t_q$	turn-off time	$V_R = 100 V; I_T = 300 A; V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^\circ C$ $di/dt = 10 A/\mu s; dv/dt = 50 V/\mu s; t_p = 200 \mu s$		350		μs

**Package Y1**

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$I_{RMS}$	RMS current	per terminal			600	A
$T_{VJ}$	virtual junction temperature		-40		140	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				650		g
$M_D$	mounting torque		4,5		7	Nm
$M_T$	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	25,0			mm
$V_{ISOL}$	isolation voltage	$t = 1$ second $t = 1$ minute	4800 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V V



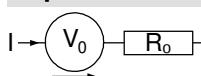
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.#(33-36)

**Part description**

M = Module  
C = Thyristor (SCR)  
M = Thyristor  
A = (up to 1800V)  
650 = Current Rating [A]  
MT = 1~ Triac  
1400 = Reverse Voltage [V]  
N = Three Quadrants operation: Q1 - QIII  
KD = Y1-2-CU

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA650MT1400NKD	MCMA650MT1400NKD	Box	2	518703

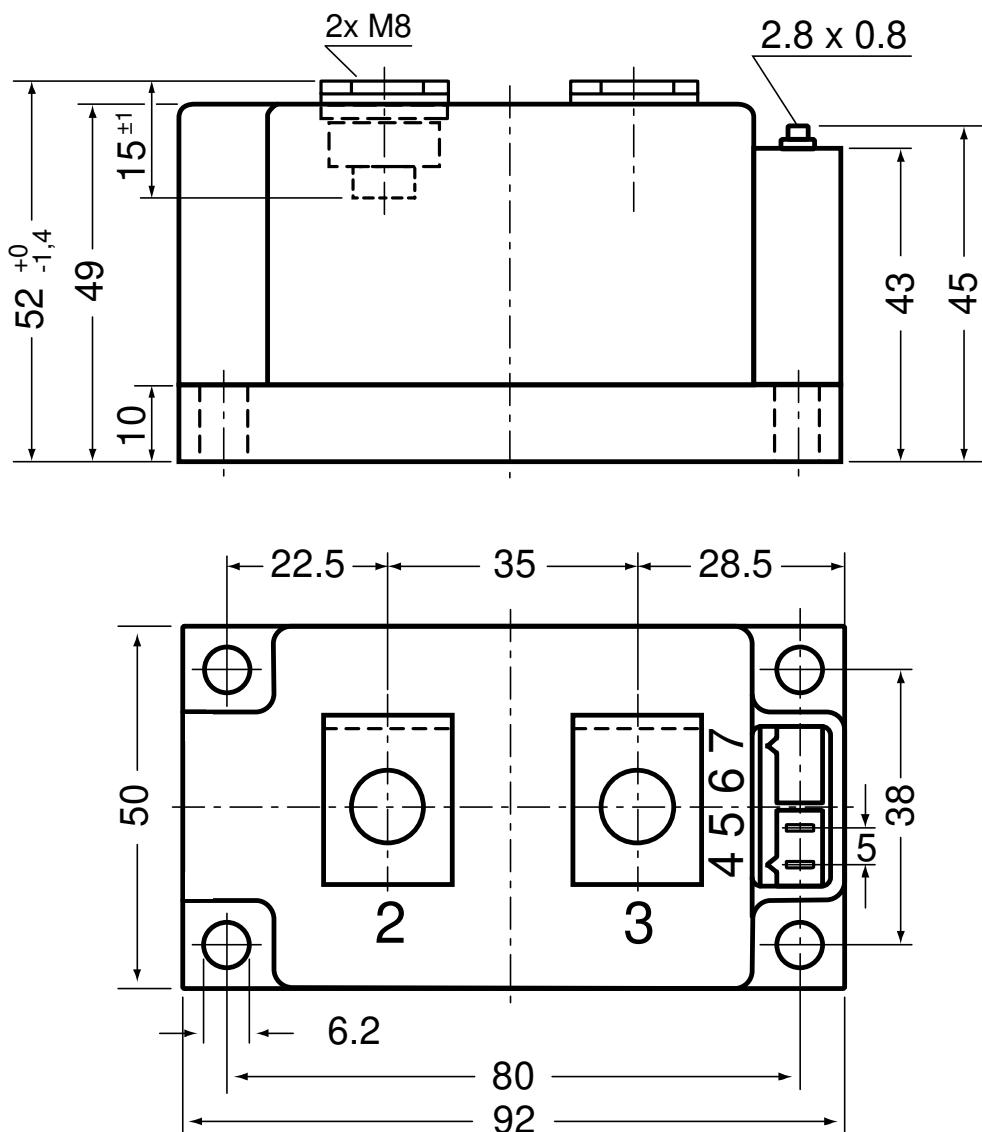
Similar Part	Package	Voltage class
MCMA650MT1800NKD	Y1-2-CU	1800

**Equivalent Circuits for Simulation**
\* on die level
 $T_{VJ} = 140^\circ\text{C}$ 

**Thyristor**

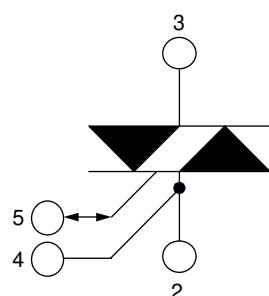
$V_{0\ max}$	threshold voltage	0,81
$R_{0\ max}$	slope resistance *	0,5

V

mΩ

**Outlines Y1**

**Optional accessories for modules**

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



## Thyristor

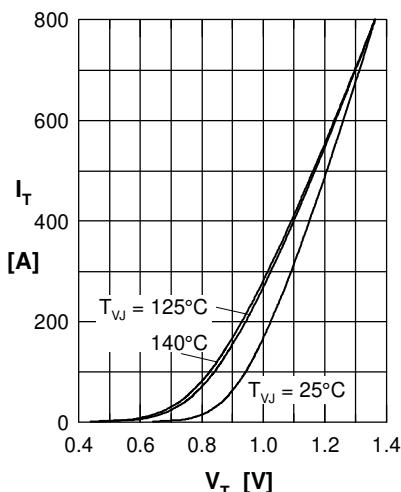


Fig. 1 Forward characteristics

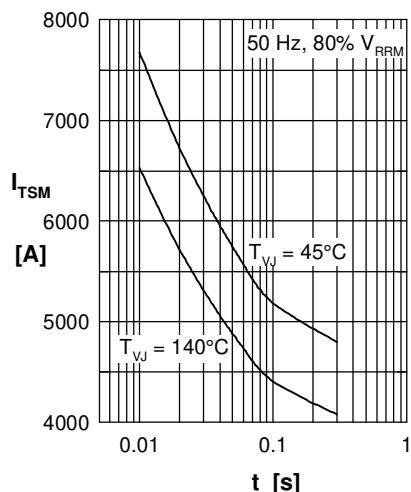


Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

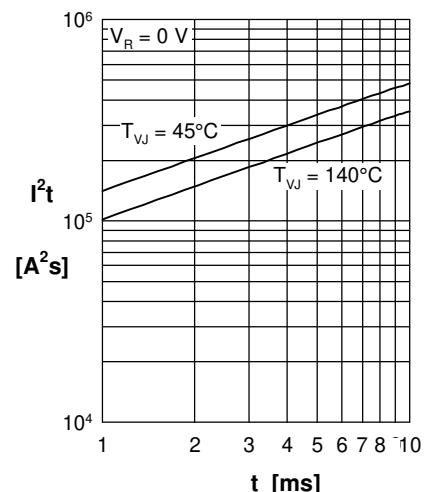


Fig. 3  $I^2t$  versus time (1-10 s)

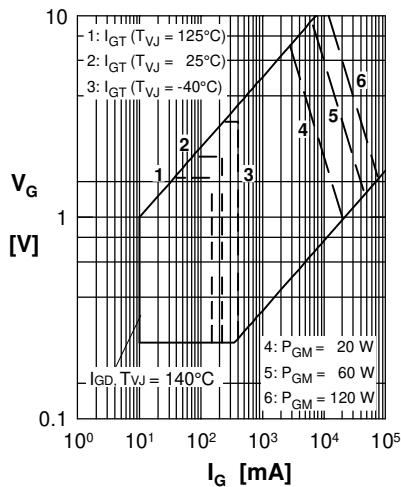


Fig. 4 Gate voltage & gate current

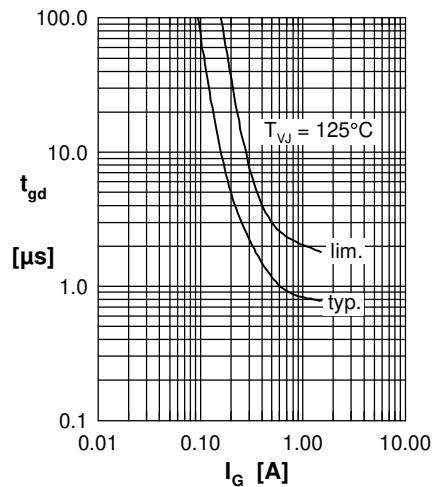


Fig. 5 Gate controlled delay time  $t_{gd}$

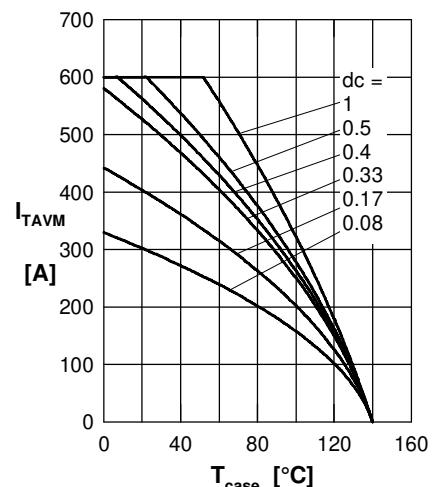


Fig. 6 Max. forward current at case temperature

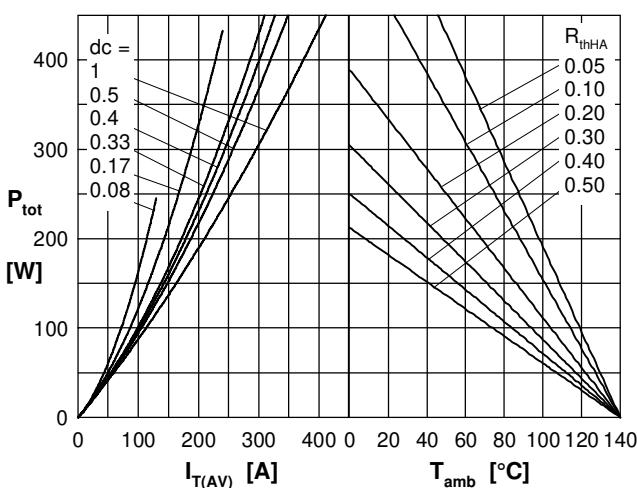


Fig. 7a Power dissipation versus direct output current  
Fig. 7b and ambient temperature

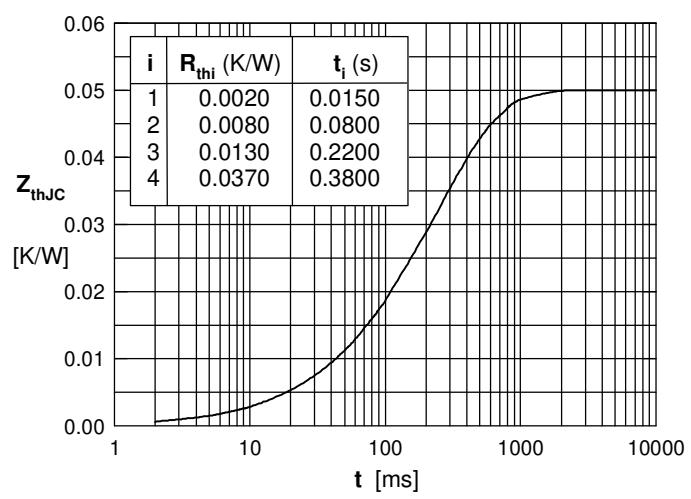


Fig. 8 Transient thermal impedance junction to case